

L Number	Hits	Search Text	DB	Time stamp
1	1885	((438/149) or (438/151) or (438/161) or	USPAT;	2003/04/06 17:41
		(438/164) or (438/166)).CCLS.	US-PGPUB	
2	99764	irradiate or irradiation	USPAT;	2003/04/06 17:45
] _	F 0 F	(///20/1/0) //20/151) //20/1/01	US-PGPUB	2002/04/06 12 16
3	595	(((438/149) or (438/151) or (438/161) or (438/164) or (438/166)).CCLS.) and	USPAT; US-PGPUB	2003/04/06 17:46
		(irradiate or irradiation)	US-FGFUD	
4	1217179	metal	USPAT;	2003/04/06 17:46
			US-PGPUB	
5	497		USPAT;	2003/04/06 17:46
		(438/164) or (438/166)).CCLS.) and (irradiate or irradiation)) and metal	US-PGPUB	
6	622038	channel	USPAT;	2003/04/06 17:46
	<i>\$22000</i>		US-PGPUB	
7	458	(((((438/149) or (438/151) or (438/161) or	USPAT;	2003/04/06 17:48
		(438/164) or (438/166)).CCLS.) and	US-PGPUB	
		(irradiate or irradiation)) and metal) and		
8	325606	channel semiconductor	USPAT;	2003/04/06 17:48
0	323000	Bemiroundacioi	US-PGPUB	2003/04/00 1/:48
9	451	((((((438/149) or (438/151) or (438/161)	USPAT;	2003/04/06 17:48
	· ·	or (438/164) or (438/166)).CCLS.) and	US-PGPUB	
		(irradiate or irradiation)) and metal) and		
10	661700	channel) and semiconductor	IICDAM.	2003/04/06 17:50
10	661709	protrusion or project or projection	USPAT; US-PGPUB	2003/04/00 17:50
11	141	(((((((438/149) or (438/151) or (438/161)	USPAT;	2003/04/06 17:50
		or (438/164) or (438/166)).CCLS.) and	US-PGPUB	
		(irradiate or irradiation)) and metal) and		
		channel) and semiconductor) and		
_	Ω	(protrusion or project or projection) (heat adj absorb\$3) with insulat\$3 with	USPAT;	2002/08/14 11:43
	O	((non-single or poly or polycrystalline)	US-PGPUB;	2002,00,14 11.40
		adj (film or layer)) with recrystalliz\$4	EPO; JPO;	
			DERWENT;	
	^	(heat add absorbed) and inculated and	IBM_TDB	2002/00/14 11.47
-	2	(heat adj absorb\$3) and insulat\$3 and ((non-single or poly or polycrystalline)	USPAT; US-PGPUB;	2002/08/14 11:47
		adj (film or layer)) and recrystalliz\$4	EPO; JPO;	
		· · · · · · · · · · · · · · · · · ·	DERWENT;	
		(1)	IBM_TDB	2000/00/14 12 22
-	6766	(heat adj absorb\$3) and insulat\$3	USPAT;	2002/08/14 12:01
			US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2	,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	USPAT;	2002/08/14 11:48
		((non-single or poly or polycrystalline)	US-PGPUB;	
		adj (film or layer)) and recrystalliz\$4	EPO; JPO; DERWENT;	
			IBM TDB	
-	0	, , ,	USPĀT;	2002/08/14 12:04
		insulat\$3 and amorphous and ((non-single	US-PGPUB;	
		or poly or polycrystalline) adj (film or	EPO; JPO;	
		layer)) and recrystalliz\$4	DERWENT; IBM TDB	
_	0	((heat adj absorb\$3) with metal) and	USPAT;	2002/08/14 12:05
	_	insulat\$3 and (( amorphous or non-single	US-PGPUB;	
		or poly or polycrystalline) adj (film or	EPO; JPO;	}
		layer)) and recrystalliz\$4	DERWENT; IBM TDB	
_	1320	(heat adj absorb\$3) with metal	USPAT;	2002/08/14 12:15
	1020	1au aaj aaddaaqo, nadii modaa	US-PGPUB;	,,
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	

-	499	((heat adj absorb\$3) with metal ) and insulat\$3	USPAT; US-PGPUB; EPO; JPO;	2002/08/14 12:06
			DERWENT; IBM TDB	
_	4	(((heat adj absorb\$3) with metal ) and insulat\$3) and (non-single or poly or	USPĀT; US-PGPUB;	2002/08/14 12:08
		polycrystalline) and recrystalliz\$4	EPO; JPO; DERWENT;	
_	24	(((heat adj absorb\$3) with metal ) and insulat\$3) and (non-single or poly or	IBM_TDB USPAT; US-PGPUB;	2002/08/14 12:08
		polycrystalline)	EPO; JPO; DERWENT;	
_	1888852		IBM_TDB USPAT;	2002/08/14 18:08
		film)	US-PGPUB; EPO; JPO; DERWENT;	
_	13	(heat adj absorb\$3 with metal) adj (layer	IBM_TDB USPAT;	2002/08/14 12:19
		or film)	US-PGPUB; EPO; JPO; DERWENT;	
_	538	(heat adj absorb\$3) adj (layer or film)	IBM_TDB USPAT;	2002/08/14 12:39
			US-PGPUB; EPO; JPO;	
_	1	(((heat adj absorb\$3) adj (layer or film))	DERWENT; IBM_TDB USPAT;	2002/08/14 12:21
		same metal) and polycrystalline	US-PGPUB; EPO; JPO;	
_	0	(((heat adj absorb\$3) adj (layer or film))	DERWENT; IBM_TDB USPAT;	2002/08/14 12:21
		same metal) and recrystalliz\$4	US-PGPUB; EPO; JPO;	2002/00/14 12.21
	105	((heat adj absorb\$3) adj (layer or film))	DERWENT; IBM_TDB USPAT;	2002/08/14 12:22
		same metal	US-PGPUB; EPO; JPO;	2002/06/14 12:22
	1	//back add abaamb(2) add /laway ay film))	DERWENT; IBM_TDB	2002/00/14 12 20
-	1	((heat adj absorb\$3) adj (layer or film)) with tft	USPAT; US-PGPUB; EPO; JPO;	2002/08/14 12:39
			DERWENT; IBM_TDB	
_	20154	((heat adj absorb\$3 or metal) adj layer or film) and tft	USPAT; US-PGPUB; EPO; JPO;	2002/08/14 15:18
			DERWENT; IBM_TDB	
_	3477	(((heat adj absorb\$3 or metal) adj layer or film) and tft) and polycrystalline	USPAT; US-PGPUB; EPO; JPO;	2002/08/14 15:19
			DERWENT; IBM_TDB	
-	2873	<pre>((((heat adj absorb\$3 or metal) adj layer or film) and tft) and polycrystalline) and insulat\$3</pre>	USPAT; US-PGPUB;	2002/08/14 15:20
		±115U±αυγ3	EPO; JPO; DERWENT; IBM_TDB	
_	0	<pre>(((((heat adj absorb\$3 or metal) adj layer or film) and tft) and polycrystalline) and insulat\$3) and irradat\$3</pre>	USPAT; US-PGPUB;	2002/08/14 15:21
		THOUTACAD! AND TITANACAD	EPO; JPO; DERWENT; IBM_TDB	
		<del></del>	·····	*···· · · · · · · · · · · · · · · · · ·

-	1208	i i i i i i i i i i i i i i i i i i i	USPAT;	2002/08/14 15:22
	İ	or film) and tft) and polycrystalline) and	US-PGPUB;	
		insulat\$3) and crystalliz\$5	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	628	' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' '	USPAT;	2002/08/14 15:22
	į	layer or film) and tft) and	US-PGPUB;	
		polycrystalline) and insulat\$3) and	EPO; JPO;	
		crystalliz\$5) and island\$1	DERWENT;	
			IBM_TDB	
_	615	((((((heat adj absorb\$3 or metal) adj	USPAT;	2002/08/14 15:23
		layer or film) and tft) and	US-PGPUB;	
		polycrystalline) and insulat\$3) and	EPO; JPO;	ļ
		crystalliz\$5) and island\$1) and	DERWENT;	
		semiconductor	IBM_TDB	
_	35	1	USPAT;	2002/08/14 18:12
		layer or film) and tft) and	US-PGPUB;	
		polycrystalline) and insulat\$3) and	EPO; JPO;	
		crystalliz\$5) and island\$1) and	DERWENT;	
		semiconductor) and protrusion\$1	IBM TDB	
-	0	irradat\$4 with protrusion\$1	USPAT;	2002/08/14 17:14
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	400	irradiat\$4 with protrusion\$1	USPAT;	2002/08/14 17:23
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	1	(irradiat\$4 with protrusion\$1) with tft	USPAT;	2002/08/14 17:16
			US-PGPUB;	2002/00/14 17:10
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	0	((irradiat\$4 with protrusion\$1) with tft)	USPAT;	2002/08/14 17:17
		with crystalliz\$5	US-PGPUB;	2002/00/14 17:17
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	0	((irradiat\$4 with protrusion\$1) with tft)	USPAT;	2002/08/14 17:17
		and crystalliz\$5	US-PGPUB;	2002/08/14 17:17
			EPO; JPO;	
			DERWENT;	]
			IBM TDB	
_	24	irradiat\$4 with (protrusion\$1 same	USPAT;	2002/09/14 17.22
		semiconductor)	US-PGPUB;	2002/08/14 17:23
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	220	irradiat\$4 and (protrusion\$1 same	USPAT;	2002/09/14 17 04
i		semiconductor)	•	2002/08/14 17:24
			US-PGPUB;	
			EPO; JPO;	
İ	]		DERWENT;	
<u> </u>	0	metal with insulat\$3 with amorphous with	IBM_TDB	2002/00/14 10 05
i		irradat\$4	USPAT;	2002/08/14 18:06
		111444671	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	21	metal and insulated and amountains and	IBM_TDB	2002/00/11 12
		metal and insulat\$3 and amorphous and irradat\$4	USPAT;	2002/08/14 18:07
		TTTUUUCYT	US-PGPUB;	
		· · · · · · · · · · · · · · · · · · ·	EPO; JPO;	
			DERWENT;	
_	121266	metal add/lavom on file	IBM_TDB	0000/00/5
	121200	metal adj(layer or film)	USPAT;	2002/08/14 18:08
		i	US-PGPUB;	
	•	į	EPO; JPO;	
			DERWENT;	
			IBM_TDB	

	101066		IIODAM.	1 2002 (20 (14 10 . 00
_	121266	metal adj (layer or film)	USPAT;	2002/08/14 18:09
			US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	3067	( metal adj (layer or film)) and tft	USPAT;	2002/08/14 18:09
	3007	( metal day (layer of lim, ) and the	US-PGPUB;	2002, 00, 11 10:03
			EPO; JPO;	
			DERWENT;	
			IBM TDB	:
_	2727	(( metal adj (layer or film)) and tft) and	USPAT;	2002/08/14 18:09
		insulat\$4	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	613		USPAT;	2002/08/14 18:11
		and insulat\$4) and crystalliz\$5	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	368	(/// motal add /lawar or film)) and tft)	IBM_TDB USPAT;	2002/08/14 18:13
_	300	(((( metal adj (layer or film)) and tft) and insulat\$4) and crystalliz\$5 ) and	US-PGPUB;	2002/00/14 18.13
		irradiat\$4	EPO; JPO;	
		1114414071	DERWENT;	
			IBM TDB	
_	53	((((( metal adj (layer or film)) and tft)	USPĀT;	2002/08/14 18:13
		and insulat\$4) and crystalliz\$5 ) and	US-PGPUB;	
		irradiat\$4) and (semiconductor adj island)	EPO; JPO;	
			DERWENT;	
	,		IBM_TDB	
_	53		USPAT;	2002/08/14 18:14
		and insulat\$4) and crystalliz\$5 ) and	US-PGPUB;	
		irradiat\$4) and (semiconductor adj	EPO; JPO;	
		island)) and electrode	DERWENT;	
		tet with islanded with amountous with	IBM_TDB USPAT;	2002/08/15 10:35
_	0	_ ·	US-PGPUB;	2002/08/13 10.33
		crystalliz\$5 with irradat\$4	EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	0	tft and island\$1 with amorphous near5	USPAT;	2002/08/15 10:35
		crystalliz\$5 with irradat\$4	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	0000/55/55
_	0		USPAT;	2002/08/15 10:36
		crystalliz\$5 with irradat\$4	US-PGPUB;	
			EPO; JPO; DERWENT;	
***************************************			IBM TDB	•
_	1	tft with island\$1 with amorphous near5	USPAT;	2002/08/15 10:36
		crystalliz\$5 with irradiat\$4	US-PGPUB;	
		0-1000	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	20010045558.URPN.	USPAT	2002/08/15 15:29
-	0	20010045558.URPN.	USPAT	2002/08/15 15:29
-	2	protrusion\$1 with crystalliz\$5 adj	USPAT;	2002/08/15 19:08
		semiconductor	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		/	IBM_TDB USPAT;	2002/08/15 19:09
-	1	(rough\$4 with recrystalliz\$5) with hsg	US-PGPUB;	2002/00/13 19:09
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	0	20020036312.URPN.	USPAT	2002/08/15 19:10
[				. <del></del>

_	711	rough\$4 same recrystalliz\$5	HODAM.	10000/00/15 10 10
	,11	Todgiiva Same recrystallizas	USPAT;	2002/08/15 19:12
			US-PGPUB;	4
			EPO; JPO; DERWENT;	
			IBM TDB	
_	292	rough\$4 with recrystalliz\$5	USPAT;	2002/08/15 19:46
		10dgii 1 wien 100ly80diii203	US-PGPUB;	2002/08/13 19:46
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	8	(rough\$4 with recrystalliz\$5) with	USPAT;	2002/08/15 19:14
		amorphous	US-PGPUB;	2002/00/13 13:14
		-	EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	0	20020034845.URPN.	USPĀT	2002/08/15 19:18
<del>-</del>	15	1 1 3 3 3 3 5 7	USPAT	2002/08/15 19:23
		"5121186"   "5147820"   "5147826"		
	Ì	"5298436"   "5326722"   "5418398"		
		"5441904"   "5514621"   "5604157"		
		"5614428"   "5652156"   "5712181").PN.		
	2	6017819.URPN.	USPAT	2002/08/15 19:39
_	0	20020036312.URPN.	USPAT	2002/08/15 19:45
_	5	(rough\$4 with recrystalliz\$5) with	USPAT;	2002/08/15 19:47
		semiconductor	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	